Fingerprints of m esoscopic leads in the conductance of a m olecular w ire

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A bstract

The in uence of contacts on linear transport through a molecular wire attached to mesoscopic tubule leads is studied. It is shown that low dimensional leads, such as carbon nanotubes, in contrast to bulky electrodes, strongly a ect transport properties. By focusing on the speci city of the lead-wire contact, we show, in a fully analytical treatment, that the geometry of this hybrid system supports a mechanism of channel selection and a sum rule, which is a distinctive hallmark of the mesoscopic nature of the electrodes.

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1 Introduction

Future electronic m iniaturization m ay enter a regim e where devices are dom – inated by quantum m echanical laws and eventually reach the single-m olecule scale [1]. A lthough m olecular m aterials for electronics have already been realized [2], their im plem entation in real applications [3{5] still has to cope with challenges in utilization, synthesis, and assembly [6]. Concerning theoretical ideas and m ethods the problem is also two-sided: O n the one hand m any theoretical ideas are already footed on past pioneering work, such as the proposal

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of m olecular recti cation in 1974 [7] which was experimentally realized only 20 years later [8]. On the other hand most of the conventional methods frequently employed for characterizing transport properties in microelectronic devices, such as the Boltzmann equation, can no longer be applied at the molecular scale. Here conductance properties have to be calculated by employing full quantum mechanical approaches and by including the electronic structure of the molecules involved.

E lectron transport on the atom ic and m olecular scale becam e a topic of intense investigation since the invention of the scanning tunneling m icroscope (STM). M ore recently, studies of transm ission properties of single m olecular junctions contacted to m etallic leads [9,10] have intensi ed the interest in the basic m echanism s of conduction across m olecular bridges. The archetype of such a m olecular device can be viewed as a donor and acceptor lead coupled by a m olecule acting as a bridge. In such system s the traditional picture of electron transfer between donor and acceptor species is re-read in term s of a novel view in which a m olecule can bear an electric current [11]. M olecular bridges have been realized out of single organic m olecules [9,12], short DNA strands [10], but also as atom ic w ires [13{15]. G enerally, contact e ects alter the \intrinsic conductance of the m olecules in such experim ents and call for closer theoretical studies.

In a parallel developm ent the use of carbon nanotube (CNT) conductors has been the focus of intense experimental and theoretical activity as another promising direction for building blocks of molecular-scale circuits [16,17]. Carbon nanotubes exhibit a wealth of properties depending on their diameter, orientation of graphene roll up, and on their topology, namely whether they consist of a single cylindrical surface (single-wall) or many surfaces (multiwall) [18]. If carbon nanotubes are attached to other materials to build elements of molecular circuits, the characterization of contacts [19,20] becomes again a fundamental issue. This problem arises also when a carbon nanotube is attached to another molecular wire, a single molecule or a molecular cluster with a privileged direction of the current ow.

In the usual theoretical treatm ent of transport through m olecular w ires, the attached leads are approxim ated by a continuum of free or quasi-free states, m in icking the presence of large reservoirs provided by bulky electrodes. How – ever such an assumption m ay become inadequate when considering leads with lateral dimensions of the order of the bridged m olecule, as for CNTs [19]. The latter have been recently used as wiring elements [17], as active devices [17,21], and, attached to scanning tunneling m icroscope (STM) tips, for enhancing their resolution [22,23]. W ith a similar arrangement the ne structure of a twinned DNA m olecule has been observed [24]. However, CNT-STM in ages seem to strongly depend on the tip shape and nature of contact with the im aging substrate [25]. This calls for a better characterization of the contact

chem istry of such hybrid structures.

This paper addresses the in uence of the molecular wire-electrode contacts on the linear conductance when the spectral structure and the geometry of the electrodes plays an important rôle. This allows us to quantify to which extent mesoscopic leads may a ect the conductance. Owing to the relevance of CNT based devices, we focus on bridges between tubular leads. In previous density-functional theory based treatments the conductance through system s such as a C₆₀ molecule in between two CNTs has been calculated with high accuracy [26]. These numerical approaches showed a strong sensitivity of the current on the system geometries and strength of the molecule-CNT couplings.

In the present paper we focus on such contact e ects. As a simplem odel for an atom ic or molecular bridge we use a hom ogenous linear chain which enables us to derive analytical expressions for the conductance in a non-interacting electron approximation. In addition, we implicitly assume that no signi cant charge is transferred between the leads and them olecular bridge at equilibrium since this could lead to an electrostatic potential-induced inhom ogeneity [27]. The latter m ay hold for an all-carbon [26] structure and m akes it possible to investigate the properties of our model in the whole parameter space. The system exhibits distinct transport features depending on the num ber and strength of contacts between the molecular bridge and the interface as well as on the symmetry of the channel wave functions transverse to the transport direction. Our ndings, which are comm on for leads with tube topology, are then studied in detail for CNT leads (Fig. 1.) by analytically treating the single-particle G reen function. In particular, we demonstrate on the one hand that con qurations with only one molecule-lead contact activated give rise to complex conductance spectra exhibiting quantum features of both the molecule and the electrodes; on the other hand multiple contacts provide a mechanism for transport channel selection leading to a regularization of the conductance, entirely provided by topological arguments. Channel selection particularly highlights the rôle of m olecular resonant states by suppressing details assigned to the electrodes.

2 System and M ethod

In a tight-binding description, the ham iltonian of the entire system , H = H $_{\rm tubes}$ + H $_{\rm w\,ire}$ + H $_{\rm coupling}$, reads

$$H = \sum_{i=L;R \text{ w ire } n, n^{0}}^{X} t_{n,n^{0}} c_{n}^{Y} c_{n^{0}}$$
(1)



Fig. 1. Schematic representation of the molecular wire-carbon nanotube hybrid with single (bottom) and multiple (top) contacts.on-site energies " $= L_{*}R_{*}w$ ire are chosen to be zero.

$$X \qquad X \qquad X \qquad X \qquad X \qquad X \qquad M_{m_{L}} C_{m_{L}}^{Ly} C_{L}^{w \text{ ire}} + h \mathfrak{x} : \qquad M_{m_{R}} C_{m_{R}}^{Ry} C_{M}^{w \text{ ire}} + h \mathfrak{x} : :$$

Here, the matrix element $t_{n \ m^0} = "_{n \ m^0} m^{0} m^{0}$ is contains the on-site energy of each of the $n_{wire} = 1; \ldots; N$ chain-atom s, "^{wire}, the orbital energy relative to that of the lead atom s, "^{L,R}, and ^{L,R}, ^{wire}, and are nearest neighbour hopping terms between atoms of the left or right leads, molecular bridge, and the bridge/lead interface, respectively. Note that $n_{L,R}$ is a two-dimensional coordinate spanning the tube lattice. Sum mations over m_L and m_R run over interfacial end-atom s of the leads. In general, there are M such atom ic positions, de ning the perimeter of the tube ends. The number of hybridization contacts between a tube and the bridge range between M_c = 1 (single contact case, SC) and M_c = M (multi-contact case, MC). Typical real molecular wires are -conjugate carbon chains with thyol end groups which in the present treatment are replaced by the linear chain model.

Since the major results we present are not qualitatively a ected by the use of more realistic quantum them ical models which take into account the precise structure and properties of the molecular bridge and of the attached leads, we keep the description of our problem at the level of the tight-binding model. In order to highlight the topological properties of tubular leads, we the sim plest case in which periodic boundary conditions are imposed on sem iin nite square lattice stripes, with the cuts parallel to the lattice bonds. We call this electrode specie square lattice tubes (SLT). In the case of CNT, when the graphene honeycom b lattice is rolled along the lattice bonds such that ' hexagons are transversally wrapped, an arm chair single wall ('; ') nanotube is obtained, and M = 2'. A coording to Eq. (1) CNT are then described at the single-band tight-binding level for orbitals. This is equivalent to assum e that am ong the four valence carbon orbitals no interaction between the

 $(2s \text{ and } 2p_{x,y})$ and orbital is signi cant because of their di erent symmetries. The fourth electron, a p_z orbital, determines the electronic properties which can be calculated by means of a tight-binding treatment, on the same level as we treat the molecular bridge. There are two such electrons per unit cell in a honeycomb structure, the and band, rendering the electronic properties of the material interesting, i.e. it can be a priori either metallic or semiconducting [28].

We study quantum transport in the fram ework of the Landauer theory [29] which relates the conductance of the system in the linear response regime to an independent-electron scattering problem [30]. The electron wavefunction is assumed to extend coherently across the whole device. The two-term inal conductance g at zero temperature is simply proportional to the total transmittance, T (E_F), for injected electrons at the Ferm i energy E_F :

$$g = 2e^2 = h T (E_F)$$
: (2)

The factor two accounts for spin degeneracy. The transmission function can be calculated from the know ledge of the molecular energy levels, the nature and the geometry of the contacts. One can see this by expressing the G reen function matrix of the full problem, $G^{-1} = G^{\text{wire}-1} + {}^{-\text{L}} + {}^{-\text{R}}$, in term softhe bare wire G reen function and the self-energy correction due to the presence of the leads. M aking use of the F isher-Lee relation [31] one can nally write

$$T(E) = 4 Tr^{n} (E)G(E)^{R}(E)G^{Y}(E)^{o};$$
 (3)

where

(E) =
$$\frac{i}{2}$$
 (z) $y(z) = \frac{i}{z^2 + i0^+}$: (4)

For the system under investigation where only the rst and last atom of the chain is coupled to the leads, the form ula for the transm ission simpli es to

$$T(E) = 4 {}^{L}(E) {}^{R}(E) {}^{J}G_{1N} (E) {}^{2};$$
(5)

where the spectral densities ^L and ^R are the only non-zero elements ^L and ^R, respectively, of the matrices . The matrix element ^{L(R)} is the spectral density of the left (right) lead. It is related to the sem i-in nite lead G reen function matrix $G^{L(R)}$. It is minus the imaginary part of the lead self-energies (per spin),

$$= i = \begin{bmatrix} X \\ m & m & 0 \end{bmatrix} = \begin{bmatrix} X \\ m & m & 0 \end{bmatrix}$$
(6)

with = L; R.Ow ing to the causality of self-energy, its real part can be entirely derived from the knowledge of via a Hilbert transform.

The rhs of Eq. (5) coincides with form ulas used to describe electron transfer in m olecular system s [32]. The above relationship between the Landauer scattering m atrix form alism on the one side and transfer ham iltonian approaches on the other side has been worked out in the recent past [11,33] showing de facto their equivalence. This enables us to make use of the form ulas from a Bardeen-type picture in terms of spectral densities, which is often convenient for an understanding and analysis of results obtained.

3 Molecular Green function

O ne has to calculate from the N N m atrix, $G^{w \text{ ire } 1} = E + i0^+$ $H_{w \text{ ire}}$, the G reen function m atrix element G_{1N} needed in Eq. (5). This m atrix element refers to the two ends of the N -atom -m olecule. Its computation requires an N N m atrix inversion. Since only the molecular-end on-site energies are perturbed by the interaction with the leads via the self-energies , some general conclusions can already be drawn without an explicit computation of G_{1N} , namely one can write [34]

$$G_{1N} = \frac{G_{1N}^{\text{wire}}}{(1 \quad {}^{L}G_{11}^{\text{wire}}) (1 \quad {}^{R}G_{NN}^{\text{wire}}) \quad {}^{L} \quad {}^{R} \left(G_{1N}^{\text{wire}}\right)^{2}}:$$
(7)

The interaction with the leads dresses, via the self-energy , the bare molecular wire G reen function element G_{1N}^{wire} . The latter can be calculated analytically in the case of a hom ogeneous wire ($n_n^{wire} = n_n^{wire}$, $m_n^{o_1} = w^{ire}$). In fact, upon projecting on the N dimensional molecular wire basis, the determinant of the bare molecular G reen matrix factorizes into a dimensionless function of only the number of chain atoms, and of the ratio $w^{ire} = (E_{n_n}^{wire}) = (2^{wire})$. This leads to a closed form for them olecular contribution to the conductance. Namely, one can easily check that $G_{1N}^{wire} = w^{ire^N}$

(wire)
1
 $_{0}$ = $_{N}$, and G $^{wire}_{11}$ = G $^{wire}_{N N}$ = $^{wire}_{N N}$ 1 = $_{N}$, where the exact form of reads:

$$\int_{N}^{w \text{ ire }} = \frac{q}{(w \text{ ire })^{2}} \int_{1}^{N+1} w \text{ ire } \frac{q}{(w \text{ ire })^{2}} \int_{1}^{N+1}$$

A fter som e algebra one nds that possesses the recursive property $_{N} _{N} _{2} = \frac{2}{N} _{1} _{0} _{0}$, which leads us to re-write Eq. (7) as

$$\frac{0}{\text{wire}G_{1N}} = N \qquad \frac{L}{\text{wire}} + \frac{R}{\text{wire}} + \frac{L}{\text{wire}^2} N_{1} + \frac{L}{\text{wire}^2} N_{2}; \qquad (8)$$

In other words, the inverse G reen function m atrix element connecting left and right leads can be written as a sum of terms, representing the inverse of the bare G reen function m atrix elements for a wire of N, N 1, and N 2 atom s. In the lim it of weak contact coupling, the behavior of the G_{1N} element is dom inated by N, leading to N transm ission resonances in the conductance of unit height. Nevertheless, if the elective coupling between the molecule and the lead is much larger than ${}^{\text{wire}}$, ${}_{\text{N}}$ 2 will become the dom inant term. As a consequence the conductance spectrum is e ectively that of an (N 2) atom ic wire [35]. The resonant behavior inside the wire band (j^{wire}j 1) and its modi cation due to the lead coupling is easily understood by writing the transmission as $T = 4^{2} \sin^{2}(\#) = D$ where the denominator D takes the following compact exact form valid for all N 1:

$$D = \sin (N + 1) \# ^{2} \sin (N - 1) \# 2 \sin N \#^{2}$$

+ 4 (sin N # sin (N - 1) #):

Here = $i = e^{w i re}$ is the self-energy of the leads (for simplicity assumed to be equal) normalized by the wire hopping. The parameter

is real in the wire band giving rise to resonances for injected electrons m atching the wire eigenenergies. Outside the wire band # is pure imaginary (sin functions are e ectively sinh functions), and the transm ission has a power law dependence on energy and an exponential dependence on the wire length, that is

 $T j^{2^{\text{wire}}j^{2N}} \text{ for } j^{\text{wire}}j 1;$ (10)

in agreem ent with previous results [36]. This analytic expression for the transm ission provides the generalization of existing results [32,33,37] to the case with non-vanishing real part of the self-energies. The density of states N =

In TrfGg = can also be written in a closed analytical form .0 ne can therefore take advantage of the fact that, due to the wire hom ogeneity, all thediagonal elements except the rst and the last one coincide,

$$G_{kk} = \frac{1}{wire} \frac{N + 1}{N} \frac{2 + 2}{N} \frac{2}{N} \frac{3}{2}$$

By using the param etrization (9) one can easily recast the density of states into the compact form

$$N = \frac{1}{\frac{1}{\text{wire}}}$$

$$\lim \frac{N \sin N \# 2(N - 1) \sin (N - 1) \# + (N - 2^{2}) \sin (N - 2) \#}{\sin (N + 1) \# - 2 \sin N \# + 2 \sin (N - 1) \#}$$

4 Electrode self-energy

In calculating the spectral function, we make use of the assumption of identical left and right leads and drop the self-energy indices in Eq. (6). Since the Ham iltonian is discrete, we can write the lattice G reen function $G = (E + i0^+ H)^{-1}$ in matrix form by rearranging the two dimensional n lattice coordinate in Eq. (1). We assume the x direction to be parallel to the tubes (and to the transport direction) and y to be the nite transverse coordinate (see Fig. 1). The latter is curvilinear with n_y spanning M sites with periodic boundary conditions.

The lattice representation of the lead G reen function is needed in the calculation of the self-energy contribution. It can generally be written by projecting the G reen operator onto the localized state basis, $k_x;k_y$ ($n_x = border;n_y$) = $k_x = k_y$ (n_y), of the sem i-in nite lead:

$$G_{n_{y}n_{y}^{0}}(E) = \overset{D}{n_{y}} E + i0^{+} H \overset{1}{n_{y}^{0}}$$
$$= \frac{X}{k_{x},k_{y}} \frac{k_{x} k_{y} (n_{y})}{E + i0^{+} E_{k_{x},k_{y}}}$$
(11)

4.1 One-dimensional electrodes: Newnsmodel

We est recall the particular case of linear chain electrodes (onto which we will map our system due to the validity of a channel selection). For such a simple model the dispersion relation as a function of the lattice on-site energies ", of the hopping terms , and of the lattice spacing a is simply given by $E = "2 \cos k_{\rm s}a$. As a result the surface G reen function for the sem in nite chain is obtained by inserting the wave function at the lead origin $k_x = 2 = \sin k_x a$ in the de ning expression (11) and transform ing the only sum over momenta into an integral, due to the in nite system size. Thus,

$$G(E) = \frac{a}{a} \int_{a}^{Z^{a}} dk_{x} \frac{\sin^{2} k_{x} a}{E + i0^{+} + 2 \cos k_{x} a} = \frac{e^{ik_{x}(E)a}}{E + i0^{+} + 2 \cos k_{x} a}$$

where we solved the integral according to Refs. [38] and we made use of the dispersion relation. The resulting spectral density, given by Eq. (6), is the sem i-elliptical local density of states (LDOS) as obtained by Newns in his theory of chem isorption [39]:

Newns () =
$$\frac{2}{e} q \frac{1}{1} \frac{2}{2}$$
 (1 j):

 $_{\rm e}$ is the strength of the single contact between the m olecule and the sem i- in nite one-dimensional leads, = (E ")=(2) is the band-norm alized energy, and the H eaviside function. The realpart of the self-energy, responsible for shifting the m olecular resonances, is simply proportional to $\cos k_x a$ and thus linear in energy. Its full dependence on energy is given by H ilbert transform ing , and it reads

Re =
$$\frac{2}{e}$$
 q _____ 2 1 ((1) (1)):

4.2 Square lattice tubular electrodes

Square lattice leads are characterized by periodic boundary conditions perpendicularly to the lead direction. Transverse momentum quantization leads to $k_y^j a = 2 \quad j=M$ (with 0 j < M). The surface G reen function for such a system can be written as

$$G_{n_{y}n_{y}^{0}}(E) = \frac{a}{M} \sum_{k_{y}=a}^{X} dk_{x} \frac{\sin^{2}(k_{x}a) '_{j} n_{y} '_{j} n_{y}^{0};}{E + i0^{+} "+ 2 \cos k_{y}a + 2 \cos k_{x}a}$$
$$= \frac{1}{M} \sum_{j=0}^{M_{x}-1} '_{j} n_{y} G^{j}(E) '_{j} n_{y}^{0}; \qquad (12)$$

where $G^{j}(E) = e^{ik_{x}^{j}(E)a} = has been obtained by solving an integral form ally equivalent to the linear chain case and using the dispersion relation$

$$E = " 2 \cos k_v^j a + \cos k_x^j (E) a :$$
 (13)

The transverse pro le of the wave function is given by $'_{j}(n_{y}) = \exp(ik_{y}^{j}n_{y}a)$. Note that the wave function is obtained by a further normalization, namely $= ' = (M \ a)^{1=2}$.

The self-energy nally reads as a sum of weighted longitudinal wave function proles

$$= \frac{1}{M} M_{j=0}^{M_{X} 1} G^{j}(E)_{j=M} [];$$

where the weight

$$j=M [] = \prod_{m=0}^{M_{X} 1} (m)^{2} (m)$$
(14)

is the contact-averaged transverse wave function. Depending on the contact geometry one has to specify the distribution of the $_{\rm m}$ contacts to calculate the weight and thus the self-energy. Note that $_{()}$ is form ally the square modulus of the Fourier series of $_{()}$; thus the zero-mode transverse momentum state j = 0 contributes to with the square of the mean contact strength. Due to the geometry of the lead surface, it is reasonable to assume a uniform distribution of contacts between the molecular wire and the electrodes. For contacts of equal strength $_{\rm m} = _{\rm e} = \frac{{\rm P} {\rm M}}{{\rm C}}$, active on M c M sites, we obtain a modulation for the contributing channels governed by

$$_{j=M}$$
 ($_{e}$; M_{c}) = $_{e}^{2}$ $M_{c} \frac{\sin c^{2} (jM_{c}=M)}{\sin c^{2} (j=M)}$;

where sinc (x \notin 0) sin (x)=x, and sinc (x = 0) 1. One can decompose the spectral density into a sum over the spectral densities of each state j. Namely = ${}^{(0)}{}^{P}_{j}w_{j}(E)$, with ${}^{(0)} = {}^{2}_{e}M_{c} = (M)$. The channel weights



Fig. 2. Spectral weights $w_j(E)$ plotted for di erent contact values M_c ; a nonlinear grey level scale is used with black corresponding to 0 and white to 1; sm all weights are am pli ed for better visualization. In every panel the horizontal axis represents the normalized energy 2 (E ")=(2) 2, and the vertical axis the normalized wave number 0 j=M < 1. Note that in the mesoscopic limit, $M_c=M$. 1, the states $j \in 0$ m atch the nodes of $_j(E)$: only the zero-transverse momentum j = 0 contributes to transport (a better resolution gure is available upon request).

are obviously independent upon rotation of the interfacial coupling position as itself is.

In Fig.2., the weights $w_{\rm j}\,(\!E$) are visualized for di erent contact values 1 M $_{\rm c}$ $\,$ 6.

For the case M = M_c the contributions from all states are suppressed except the state with zero transverse momentum, which is the outcome of the sum rule (14). That is, = ${}_{e}^{2}$ M_{j;0}. Thus the conguration with all contacts of the tube ends coupled to the molecule with strength ${}_{e} = \overline{M}$ is equivalent to the case of a single contact with strength ${}_{e}$ to a one-dimensional lead (previous section). Moreover a scaling law is found for , and a fortiori for the conductance given by g = g $\overline{M_{c}}$, where is the local contact strength.

In Fig. 3, is displayed as a function of energy, lead diam eters and active contacts. As easily visible, it is only for values M $_{\rm c}$ of the order of the available contacts M that the m esoscopic nature of the scattering channels enter the spectral density. The larger the tube diam eter the lower is the number of contacts which are needed to reach a M C -like spectral density. This observa-



Fig. 3. The normalized spectral density $= \frac{2}{e}$ plotted for different maximum values M_c as in Fig. 2.; the x-axes represent the normalized energies 2 (E ")=(2) 2, the y-axes label the dimensionality of the leads (number of possible contacts) M_c M 20 (a better resolution gure is available upon request).

tion justi es the use of the one-dim ensional Newns model for leads of lateral dim ension much larger than the contacted molecule but also shows the lim it of this approach when dealing with quasi-onedim ensional leads. It remains to investigate to which extent the results obtained so far can be generalized to realistic quasi-onedim ensional structures such as CNT.

4.3 Carbon nanotube electrodes

W hen the arm chair ('; ') CNT topology is in posed the number of carbon sites at the interface is M = 2'. The eigenvalues of the tight-binding ham iltonian (1),

$$E \quad k_{x}^{j}; j = " \quad \overset{V_{u}^{u}}{t} \frac{j}{1 + 4\cos\frac{j}{x}\cos\frac{k_{x}^{j}a}{2} + 4\cos^{2}\frac{k_{x}^{j}a}{2}; \quad (15)$$

are obtained in a basis set given by symmetric (+) and antisymmetric (-) site congurations of the graphene bipartite lattice, corresponding to - and

orbitals respectively [28,40]. The longitudinal momentum is restricted to the B rillouin zone, $\langle k_{x}^{j}a \langle , and$ the transverse wave number 1 j 2' labels 4' bands, as many as the number of atom s in the unit cell of a (';') CNT. The two bands corresponding to j = 'are singly degenerate. They are responsible for them etallic character of arm chair carbon nanotubes (these two bands corresponding to j = 2 are singly degenerate where the sources of the set of bands corresponding to j = 2 are singly degenerate while the other remaining (4' 4) bands are collected in (2' 2) doubly-degenerate dispersion curves.

The single-particle G reen function in a lattice representation for two sites belonging to the same sub-lattice can be still written as in Eq. (12) as

$$G_{n_{y},n_{y}^{0}}(E) = \frac{1}{2} \sum_{j=1}^{X^{2}} n_{y} G^{j}(E) n_{y}^{0} ; \qquad (16)$$

where $i_j(n_y) = \exp(ik_y^j n_y a)$, with $k_y^j a = j = i$, and 1 j 2. Note that in Eq. (16), n_y and n_y^0 should be either even or odd (that is they should belong to the same sublattice). The sem i-in nite longitudinal G reen function is given by

$$G^{j}(E) = \frac{a}{8} \int_{a}^{X} dk_{x}^{j} \frac{\sin^{2}(k_{x}^{j}a=2)}{E + i0^{+} E k_{x}^{j}; j}$$

The integral can be worked out analytically by extending k_x^j to the complex plane and adding cross-cancelling paths (parallel to the imaginary axis) along the sem i-in nite rectangle in the halfplane Im $k_x^j > 0$ and based on the interval between =a and =a. The closing path parallel to the real axis gives a real contribution linear in energy. This generalizes the approach by Ferreira et al. [41], recently adopted for obtaining an analytical expression for the diagonal G reen function of in nite achiral tubes, to the case of sem i-in nite CNTs. The determ ination of the poles inside the integration contour, given by

$$\cos^{0} \frac{q^{j}a}{2}^{A} = \frac{1}{2}\cos\frac{j}{2} = \frac{1}{2}\cos\frac{j}{2} = \frac{y}{2} = \frac{z}{2} + \frac{z}{2} = \frac{z}{2} + \frac{z}{2} + \frac{z}{2} + \frac{z}{2} = \frac{z}{2} + \frac{z$$

allows for the calculation of the residues and thus of the surface G reen function. One $\ {\rm nds}$

where the choice of the contributing pole through the branch parameter = sign (E $\,$ ") has to be taken into account. The LDOS, obtained from the imaginary part of the surface G reen function after Eq. (17) is plugged into Eq. (16), is shown in Fig. 4. It clearly diers from the LDOS of an in nite CNT as depicted for comparison in the right panel. As for the case of the



Fig. 4. Left panel: the norm alized spectral density for a sem i-in nite ('; ') CNT lead in the SC con guration; it corresponds to the LDOS at any atom site at the cut of the CNT lead. For comparison the dispersion relation and the LDOS of an in nite ('; ') CNT are shown in the middle and right panel respectively. Solid lines in the dispersion relation panel indicate doubly degenerate bands, dashed lines singly degenerate bands. Here ' = 10, and on-site energies and hopping terms refer to = L;R-leads.

SLT the pinning of the longitudinal wave function at the surface of the sem iin nite systems cancels all border zone anom alies when q^j a m atches multiples of 2. In in nite SLTs these states are the only resonant states (van Hove singularities) so that the surface LDOS of a sem i-in nite SLT never diverges (as it is shown in the left panel of F ig. 5). On the contrary, in CNTs there are states with zero group velocity outside the border zone which are responsible for the singularities of the spectral density of sem i-in nite CNTs (left panel of F ig. 4).

The self-energy for a CNT lead is more complicate than the one for a SLT ow ing to them issing equivalence of the sites belonging to the two di erent sublattices. However, since the longitudinal part of the G reen function, Eq. (17), is the same for all diagonal and o -diagonal terms of the surface G reen function, the self-energy can still be cast into the form



Fig. 5. The norm alized spectral density as a function of energy and active contacts is plotted for M = 10 possible atom ic contacts available; on-site energies and hopping terms refer to $= L_{i}R$ -leads. The right panel illustrate num erical results after R ef. [42] in full agreem ent with the analytics showed in the text.

$$= \frac{1}{2} \sum_{j=1}^{2} G^{j}(E)_{j=1} []:$$

However, for the calculation of

$$_{j='}[] = \frac{X^{2'}}{_{m=1}} m'_{j}(m)^{2}; \qquad (18)$$

one has to specify the sub-lattice components of the transverse wave function and whether they belong to a bonding or anti-bonding molecular state. Again the distribution of the 🔐 contacts is needed in oder to calculate the and thus the self-energy. Eq. (18) simpli es considerably in the SC weight case: = 2 . Since is uniform in j the self-energy is simply proportional to the diagonal sem i-in nite G reen function and, as a consequence, the spectral density is proportional to the local density of states (Fig. 4.). The MC case $(m = e^{-2})$ is also easily tractable leading to a sum rule over the possible conducting channels. However a direct proof is provided by the intuitive consideration that only the -bonding state can contribute to the M C spectral density (all the other states have a non-constant spatialm odulation provided e.g. in Ref. [43]). Following our notation the -bonding state corresponds to j = '.F ig. (5) shows the spectral density in the interm ediate regime between the SC and M C limits. The two di erent lead lattice structures carry the same physical information only in the MC lim it case.

5 D iscussion and concluding rem arks

It is interesting to recollect the results for the MC -spectral density, $_{MC}$, in all three lead models considered so far.U sing the dispersion relation (13) and the surface G reen function in Eq. (12) the spectral density for SLT leads coincides form ally with the New ns LDOS with an energy shift $_{MC}^{SLT}$ () = $^{New ns}$ (+ 1). For CNTs Eqs. (15-17) lead to $_{MC}^{CNT}$ () = $^{New ns}$ + $\frac{1}{2}$. From the above discussion it is clear that them ultiple contact con guration suppresses features associated with the two-dimensional character of tubular leads, apart from an energy shift. In ourm odel, the latter is the only rem nant the system preserves from the transverse momentum component.

In contrast, the SC case is strongly dependent on the lead underlying structure. The spectral density for a single contact, $_{\rm SC}$, reduces to the LDOS in the lead at the point where the molecular wire is contacted with strength ,

 $_{SC} = ^{2} LDOS:$

It is, in particular, in the SC scenario that the conductance of the molecular wire might be strongly a ected by the nature of the leads [35]. Nevertheless, once the nature of the contact can be inferred, one can think to cure the spurious insertion in the conductance by litering out the contribution of the leads from the molecular resonances. For instance, in the CNT -enhanced STM tips [22] the improved resolution images can be cleaned by de-convolving them using model assumptions for the leads and their contact geom etry.

A nother signi cant consequence of the peculiar contact dependence of the spectral density is the possibility to understand the in uence of the mesoscopic character of the leads. In the limit of large M (at xed M_c), looses its granularity being sampled by m any m ore states compared to its nodes, whereas for M_c=M . 1 an increasing number of nodes matches the decreasing number of states. This determ ines a reduction in the self-energy, and thus in the width of the molecular resonances, highlighting the quantum features of the wire. The latter result in a quite striking behavior for CNTs because of the band anom alies outside of the border zone which strongly determ ine the resonant behavior of the spectral density.

To conclude, we have shown that novel features are expected to arise in the conductance of a molecular wire connected to nanotube leads. The commonly used approximation of a pure imaginary, at, wide band self-energy is not valid when employing tubular leads. Nevertheless, the conductance of a hom ogeneous molecular wire still possesses an analytical form in the entire regime of the wire parameters and allows for the insertions of a nonvanishing real self-energy, necessarily arising when considering nanotube leads. By tailoring

the geom etry and dimensionality of the contacts, it is possible to perform a channel selection. In the M C limit the conductance becomes independent of the lattice structure of the tubular electrodes, transport is dominated by topology properties and is electively one-dimensional. Furthermore, the conductance obeys a universal scaling law in the multiple contact conguration. We would further like to stress that the derived analytical expression for the sem i-in nite CNT self-energy allows for a full analytical treatment of the linear conductance problem. The possibility to handle an exact expression of the sem i-in nite CNT G reen function may serve as a rst step in analytical treatments of more complex carbon based molecular structures such as T- or Y-junctions [44].

6 A cknow ledgm ents

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References

- [1] Y.Taur, Proc. EEE 85 (1997) 4.
- B. Crone, A. Dodabalapur, Y. Lin, R. W. Filas, Z. Bao, A. Laduca, R. Sarpeshkar, H. E. Katz, W. Li, Nature 403 (2000) 521-523; J. H. Schon, C. K loc, E. Bucher, B. Batlogg, Nature 403 (2000) 408-410; K. Ziem elis, Nature 394 (1998) 619-620; J. M. Tour, Chem. Rev. 96 (1996) 537-554.
- [3] J.C.Ellenbogen, J.C.Love, Proc. EEE 88 (2000) 386-426.
- [4] J.M. Tour, M. Kozaki, J.M. Sem inario, J.Am. Chem. Soc. 120 (1998) 8486-8493.
- [5] D. Goldhaber-Gordon, M. S. Montemerlo, J. C. Love, G. J. Opiteck, J. C. Ellenbogen, Proc. IEEE 85 (1997) 521-540.
- [6] R.Landauer, IEEE Trans. Electron Devices 43 (1996) 1637–1639.
- [7] A.Aviram, M.A.Ratner, Chem. Phy. Lett. 29 (1974) 277-283.
- [8] D. H. Waldeck, D. N. Beratan, Science 261 (1993) 576-577; A. S. Martin, J.R. Sambles, G. J. A shwell, Phys. Rev. Lett. 70 (1993) 218-221.

- [9] M.A.Reed, C.Zhou, C.J.Muller, T.P.Burgin, J.M. Tour, Science 278 (1997) 252-254.
- [10] D. Porath, A. Bezryadin, S. de Vries, C. Dekker, Nature 403 (2000) 635-638.
- [11] A.Nitzan, Ann. Rev. Phys. Chem. 52 (2001) 681-750.
- [12] J. Reichert, R. Ochs, D. Beckmann, H. B. Weber, M. Mayor, and H.v.Lohneysen, To appear in Phys. Rev. Lett.; cond-mat/0106219.
- [13] J.M. van Ruitenbeek, Naturwissenschaften 88 (2001) 59-66.
- [14] A. I. Yanson, G. Rubio Bollinger, H. E. van den Brom, N. Agrat, J. M. van Ruitenbeek, Nature 395 (1998) 783-785.
- [15] H. Ohnishi, Y. Kondo, K. Takayanagi, Nature 395 (1998) 780-783.
- [16] A. Karlsson, R. Karlsson, M. Karlsson, A. Cans, A. Stromberg, F. Ryttsen, O. Orwar, Nature 409 (2001) 150–152.
- [17] T. Rueckes, K. Kim, E. Joselevich, G. Y. Tseng, C.-L. Cheung, C. M. Lieber, Science 289 (2000) 94–97; N. Yoneya, E. Watanabe, K. Tsukagoshi, Y. Aoyagi, App. Phys. Lett. 79 (2001) 1465.
- [18] R. Saito, G. D resselhaus, M. S. D resselhaus, Physical Properties of Carbon Nanotubes, W orld Scienti c Publishing, London, 1998; P.M & uen, Phys.W orld 13 (2000) 31-36.
- [19] C. Thelander, M. H. Magnusson, K. Deppert, L. Samuelson, P. Rugaard Poulsen, J. Nygard, J. Borggreen, App. Phys. Lett. 79 (2001) 2106-2108.
- [20] J. Hu, M. Ouyang, P. Yang, C. M. Lieber, Nature 399 (1999) 48-51; P. J. de Pablo, E. Graugnard, B. Walsh, R. P. Andres, S. Datta, R. Reifenberger, App. Phys. Lett. 74 (1999) 323-325.
- [21] V. Derycke, R. Martel, J. Appenzeller, Ph. Avouris, Nano Letters 1 (2001) 453-456; H.W. C. Postma, T. Teepen, Z. Yao, M. Grifoni, C. Dekker, Science 293 (2001) 76-79; R. Martel, T. Schmidt, H. R. Shea, T. Hertel, Ph. Avouris, App. Phys. Lett. 73 (1998) 2447-2449.
- [22] H. W atanabe, C. M anabe, T. Shigem atsu, M. Shim izu, App. Phys. Lett. 78 (2001) 2928-2930.
- [23] S.S.Wong, E. Joselevich, A.T.Woolley, C.L.Cheung, C.M. Lieber, Nature 394 (1998) 52-55.
- [24] H.Nishijim a, S.Kamo, S.Akita, Y.Nakayama, K.I.Hohmura, S.H.Yoshimura, K.Takeyasu, App. Phys. Lett. 74 (2000) 4061-4063.
- [25] S.Akita, H.N ishijim a, T.K ishida, Y.Nakayam a, Jpn.J.Appl.Phys.39 (2000) 7086-7089; A.I.Onipko, K.F.Berggren, Y.O.K lym enko, L.I.Malysheva, J.J.W.M.Rosink, L.J.Geerligs, E.van der Drift, S.Radelaar, Phys.Rev.B 61 (2000) 11118-11124; A.L.Vazquez de Parga, O.S.Heman, R.Miranda, A.Levy Yeyati, N.Mingo, A.Mart n-Rodero, F.Flores, Phys.Rev.Lett. 80 (1998) 357-360.

- [26]G. Cuniberti, R. Gutierrez, G. Fagas, F. Gromann, K. Richter, and R. Schmidt, Physica E 12 (2002) 749; R. Gutierrez, G. Fagas, G. Cuniberti, F. Gromann, R. Schmidt, and K. Richter, Phys. Rev. B 65 (2002) 113410.
- [27] N.D. Lang, Ph. Avouris, Phys. Rev. Lett. 84 (2000) 358-361.
- [28] R. Saito, M. Fujita, G. D resselhaus, M. S. D resselhaus, Phys. Rev. B 46 (1992) 1804–1811.
- [29] Y. Im ry, R. Landauer, Rev. M od. Phys. 71 (1999) S306.
- [30] D.K.Ferry, S.M.Goodnick, Transport in Nanostructures, Vol. 6 of Cambridge Studies in Sem iconductor Physics & Microelectronic Engineering, Cambridge University Press, Cambridge, 1999.
- [31] D.S.Fisher, P.A.Lee, Phys. Rev. B 23 (1981) R 6851-R 6854.
- [32] V.Mujica, M.Kemp, M.A.Ratner, J.Chem. Phys. 101 (1994) 6849-6855; ibid. pag. 6856-6864.
- [33] L.E.Hall, J.R.Reimers, N.S.Hush, K.Silverbrook, J.Chem. Phys. 112 (2000) 1510-1521.
- [34] S.S.Skourtis, J.N.Onuchic, Chem. Phy. Lett. 209 (1993) 171-177.
- [35] G. Fagas, G. Cuniberti, K. Richter, Phys. Rev. B 63 (2001) 045416.
- [36] H.M.McConnell, J.Chem. Phys. 35 (1961) 508-515.
- [37] M. Sum etskii, J. Phys. Condens. M atter 3 (1991) 2651-2654; V. V. M alov, L.V. Iogansen, Opt. Spektrosk. (USSR) 48 (1980) 146-154.
- [38] K. V. Brodovitsky, Doklady Akadem ii NAUK SSSR 120 (1958) 1178–1179; see also eq. 3.644.4 in I. S. Gradschteyn, I.M. Ryzhik, Tables of Integrals, Series, and Products, 6th Edition, Academ ic Press, Inc., San Diego, 2000.
- [39] D.M. Newns, Phys. Rev. 178 (1969) 1123.
- [40] P.R.W allace, Phys. Rev. 71 (1947) 622-634.
- [41] M.S.Ferreira, T.G.Dargam, R.B.Muniz, A.Latge, Phys.Rev.B 63 (2001) 245111; this reference contains some misprints, especially in the naldiagonal form of the Green function of an in nite CNT amended in the erratum ibid. Phys.Rev.B 65 (2002) 039901.
- [42] G. Cuniberti, G. Fagas, K. Richter, Acta Phys. Pol. 32 (2001) 437-442.
- [43] H.J.Choi, J.Ihm, Solid State Comm. 111 (1999) 385-390.
- [44] L.M. Peng, Z. L. Zhang, Z. Q. Xue, Q. D. Wu, Z. N. Gu, D. G. Pettifor, Phys. Rev. Lett. 85 (15) (2000) 3249–3252; C. Papadopoulos, A. Rakitin, J. Li, A. S. Vedeneev, J.M. Xu, Phys. Rev. Lett. 85 (16) (2000) 3476–3479.